

What is claimed is:

1. A light emitting pixel unit, comprising:
at least one mesa formed on a substrate; and
a micro-lens formed from a micro-lens layer that covers at least a top of the at least one mesa;
wherein:
material of the micro-lens layer is different from material of the at least one mesa, and
the micro-lens layer is in direct physical contact with the at least one mesa.
2. The light emitting pixel unit according to claim 1, wherein the micro-lens forms individually around the top of the at least one mesa.
3. The light emitting pixel unit according to any one of claims 1-2, wherein a spacer is formed from the same micro-lens layer between the at least one mesa and the micro-lens.
4. The light emitting pixel unit according to claim 3, wherein thickness of the spacer is not more than 1 micrometer.
5. The light emitting pixel unit according to any one of claims 3-4, wherein material of the spacer is as the same as material of the micro-lens.
6. The light emitting pixel unit according to any one of claims 1-5, wherein the micro-lens is composed of a dielectric material.
7. The light emitting pixel unit according to claim 6, wherein the dielectric material comprises silicon oxide.
8. The light emitting pixel unit according to any one of claims 1-7, wherein material of the micro-lens is photoresist.
9. The light emitting pixel unit according to any one of claims 1-8, wherein the height of the micro-lens is not more than 2 micrometers.

10. The light emitting pixel unit according to any one of claims 1-9, wherein the width of the micro-lens is not more than 4 micrometers.
11. The light emitting pixel unit according to any one of claims 1-10, wherein, on the substrate, the at least one mesa is within a matrix of mesa array, and the micro-lens is within a matrix of micro-lens array placed according to placement the mesa array.
12. The light emitting pixel unit according to any one of claims 1-11, wherein the top of the at least one mesa is flat, and the shape of the micro-lens is hemisphere.
13. The light emitting pixel unit according to any one of claims 1-12, wherein the at least one mesa includes at least a light emitting device.
14. The light emitting pixel unit according to claim 13, wherein the light emitting device includes a PN junction.
15. A method of fabricating a light emitting pixel unit, comprising:
 - providing a substrate;
 - forming at least one mesa on the substrate; and
 - depositing a micro-lens material layer directly on at least a top of the at least one mesa, wherein the micro-lens material layer is conformed to a shape of the at least one mesa and has a shape of hemisphere on the at least one mesa.
16. The method of fabricating a light emitting pixel unit according to claim 15, wherein the micro-lens material layer is deposited by a chemical vapor deposition technology.
17. The method of fabricating a light emitting pixel unit according to claim 16, wherein, parameters of the chemical vapor deposition technology used to deposit the micro-lens material layer include: power is 0 W to 1000 W, pressure is 100 milli-torr to 2000 milli-torr, temperature is 23 °C to 500 °C, gas flow rate is 0 sccm to 3000 sccm, and time is 1 hour to 3 hours.
18. The method of fabricating a light emitting pixel unit according to any one of claims 15-17, wherein the micro-lens material layer is composed of a dielectric material.

19. The method of fabricating a light emitting pixel unit according to any one of claims 15-18, further comprising: patterning the micro-lens material layer to expose an electrode area of the substrate.

20. The method of fabricating a light emitting pixel unit according to claim 19, wherein patterning further includes:

forming a mask on surface of the micro-lens material;

patterning the mask via a photolithography process, thereby forming openings in the mask and exposing the micro-lens material layer above the electrode area of the at least one mesa; and

with the mask protection in place, etching portions of the micro-lens material layer exposed by the openings.

21. The method of fabricating a light emitting pixel unit according to claim 20, wherein etching is a wet etching method.

22. A method of fabricating a light emitting pixel unit, comprising:

providing a substrate;

forming at least one mesa on the substrate;

depositing a micro-lens material layer directly on at least a top of the at least one mesa, wherein the micro-lens material layer covers the top of the at least one mesa and top surface of the micro-lens material is flat; and

patterning the micro-lens material layer from top down, thereby forming at least a hemisphere in the micro-lens material layer, without passing through the micro-lens material layer, wherein the hemisphere is placed above the at least one mesa.

23. The method of fabricating a light emitting pixel unit according to claim 22, further including:

depositing a mask layer on the surface of the micro-lens material layer;

patterning the mask layer to form a hemisphere pattern in the mask layer; and

using the hemisphere pattern as a mask, etching the micro-lens material layer to form the hemisphere in the micro-lens material layer.

24. The method of fabricating a light emitting pixel unit according to claim 23, wherein, after the micro-lens material layer is etched, the micro-lens material layer is not etched through to expose top surface of the at least one mesa, thereby a spacer is formed on the top of the at least one mesa.

25. The method of fabricating a light emitting pixel unit according to any one of claims 22-24, wherein the micro-lens material layer is deposited by spin coating.

26. The method of fabricating a light emitting pixel unit according to any one of claims 23-25, wherein the mask layer is patterned by a photolithography process firstly and then a reflowing process.

27. The method of fabricating a light emitting pixel unit according to any one of claims 23-26, wherein etching the micro-lens material layer is by a photolithography process.

28. The method of fabricating a light emitting pixel unit according to any one of claims 22-27, further comprising: after forming the at least one mesa and before depositing the micro-lens material layer, forming a mark layer with marks for aligning to the micro-lens material layer in the patterning process.

29. The method of fabricating a light emitting pixel unit according to any one of claims 22-28, further comprising: after patterning the micro-lens material layer, patterning the micro-lens material layer to expose an electrode area of the substrate.